MOSFETs Silicon P-Channel MOS (U-MOSVI)

# **TPC6130**

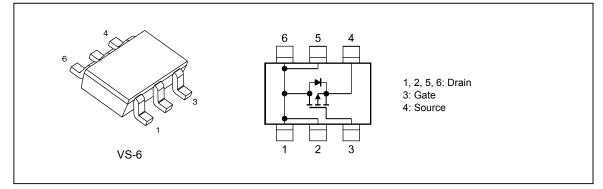
#### 1. Applications

- Lithium-Ion Secondary Batteries
- Power Management Switches

### 2. Features

- (1) Small footprint due to small and thin package
- (2) Low drain-source on-resistance:  $R_{\rm DS(ON)}$  = 86 mO (typ.) (V\_{\rm GS} = -4.5 V)
- (3) Low leakage current:  $I_{\rm DSS}$  = -10  $\mu A$  (max) (V\_{\rm DS} = -20 V)
- (4) Enhancement mode:  $V_{th} = -0.5$  to -1.2 V ( $V_{DS} = -10$  V,  $I_D = -0.2$  mA)

#### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

| Characteristics               |           |          |                  | Rating     | Unit |
|-------------------------------|-----------|----------|------------------|------------|------|
| Drain-source voltage          |           |          | V <sub>DSS</sub> | -20        | V    |
| Gate-source voltage           |           |          | V <sub>GSS</sub> | ±12        |      |
| Drain current (DC)            |           | (Note 1) | Ι <sub>D</sub>   | -2.8       | Α    |
| Drain current (pulsed)        |           | (Note 1) | I <sub>DP</sub>  | -11.2      |      |
| Power dissipation             | (t = 5 s) | (Note 2) | PD               | 2.2        | W    |
| Power dissipation             | (t = 5 s) | (Note 3) | PD               | 0.7        | W    |
| Single-pulse avalanche energy |           | (Note 4) | E <sub>AS</sub>  | 10.1       | mJ   |
| Avalanche current             |           |          | I <sub>AR</sub>  | -2.8       | Α    |
| Channel temperature           |           |          | T <sub>ch</sub>  | 150        | °C   |
| Storage temperature           |           |          | T <sub>stg</sub> | -55 to 150 |      |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

| Characteristics                       |           |          | Symbol                | Max  | Unit |
|---------------------------------------|-----------|----------|-----------------------|------|------|
| Channel-to-ambient thermal resistance | (t = 5 s) | (Note 2) | R <sub>th(ch-a)</sub> | 56.8 | °C/W |
| Channel-to-ambient thermal resistance | (t = 5 s) | (Note 3) | R <sub>th(ch-a)</sub> | 178  | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4:  $V_{DD}$  = -16 V,  $T_{ch}$  = 25°C (initial), L = 1 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = -2.8 A



Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

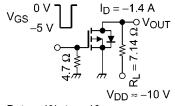
#### 6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

| Characteristics                         | Symbol               | Test Condition                                    | Min  | Тур. | Max  | Unit |
|---|----------------------|---|------|------|------|------|
| Gate leakage current                    | I <sub>GSS</sub>     | $V_{GS}$ = ±12 V, $V_{DS}$ = 0 V                  | _    | _    | ±0.1 | μA   |
| Drain cut-off current                   | I <sub>DSS</sub>     | $V_{DS}$ = -20 V, $V_{GS}$ = 0 V                  | —    | —    | -10  |      |
| Drain-source breakdown voltage          | V <sub>(BR)DSS</sub> | I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V    | -20  |      | _    | V    |
| Drain-source breakdown voltage (Note 5) | V <sub>(BR)DSX</sub> | $I_{\rm D}$ = -10 mA, $V_{\rm GS}$ = 8 V          | -12  | _    | _    |      |
| Gate threshold voltage                  | V <sub>th</sub>      | V <sub>DS</sub> = -10 V, I <sub>D</sub> = -0.2 mA | -0.5 | —    | -1.2 |      |
| Drain-source on-resistance              | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -1.4 A | _    | 128  | 164  | mΩ   |
|   |                      | V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -1.4 A | _    | 86   | 106  |      |

Note 5: If a forward bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

### 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics                | Symbol           | Test Condition  | Min | Тур. | Max | Unit |
|--------------------------------|------------------|---|-----|------|-----|------|
| Input capacitance              | Ciss             | V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz | _   | 360  | _   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> | ]   |     | 47   | _   |      |
| Output capacitance             | C <sub>oss</sub> |   |     | 63   | _   |      |
| Switching time (rise time)     | tr               | See Figure 6.2.1.   | _   | 4    | _   | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  | ]   |     | 13   | _   |      |
| Switching time (fall time)     | t <sub>f</sub>   | ]   |     | 9    | _   |      |
| Switching time (turn-off time) | t <sub>off</sub> | ]   | _   | 40   | _   |      |



Duty  $\leq$  1%,  $t_W =$  10  $\mu s$ 



#### 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics                                 | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | $V_{DD}\approx$ -16 V, $V_{GS}$ = -5 V, $I_{D}$ = -2.8 A | _   | 5.1  | _   | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |  | —   | 0.8  | _   |      |
| Gate-drain charge                               | Q <sub>gd</sub>  |  | _   | 1.8  | _   |      |

#### 6.4. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics                |          | Symbol           | Test Condition                                  | Min | Тур. | Max   | Unit |
|--------------------------------|----------|------------------|---|-----|------|-------|------|
| Reverse drain current (pulsed) | (Note 6) | I <sub>DRP</sub> | —   | —   | —    | -11.2 | А    |
| Diode forward voltage          |          | V <sub>DSF</sub> | I <sub>DR</sub> = -2.8 A, V <sub>GS</sub> = 0 V |     |      | 1.2   | V    |

Note 6: Ensure that the channel temperature does not exceed 150°C.

### 7. Marking

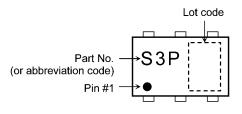
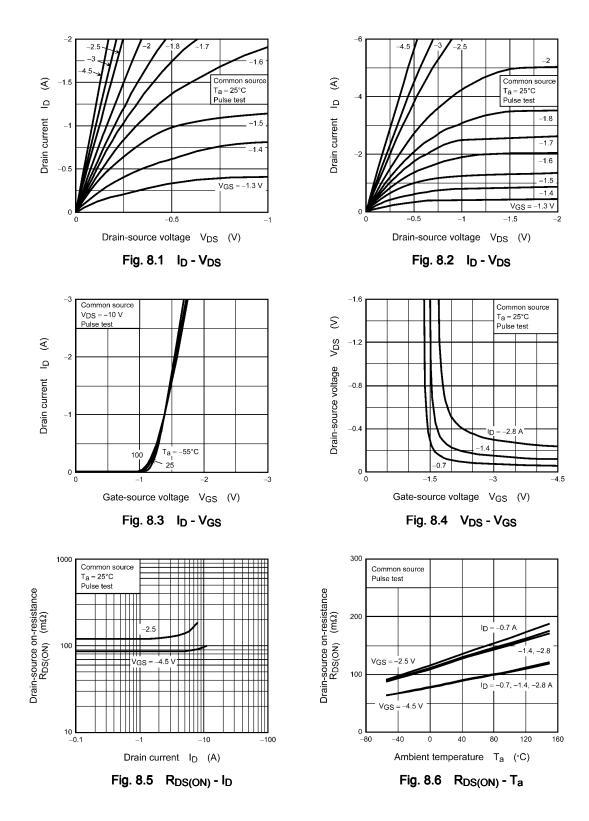
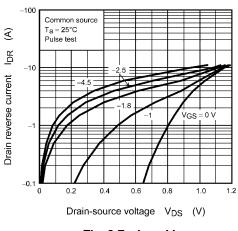


Fig. 7.1 Marking

#### 8. Characteristics Curves (Note)







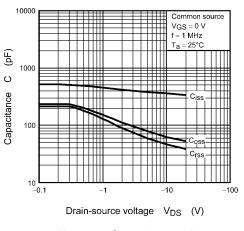


Fig. 8.8 Capacitance - V<sub>DS</sub>

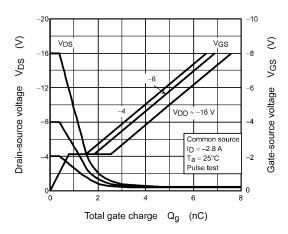
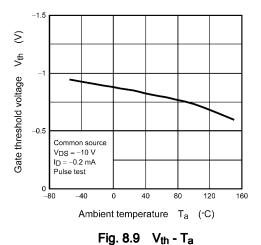
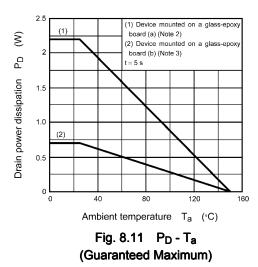


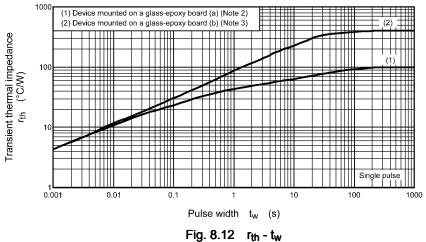
Fig. 8.10 Dynamic Input/Output Characteristics



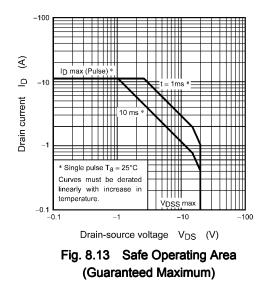


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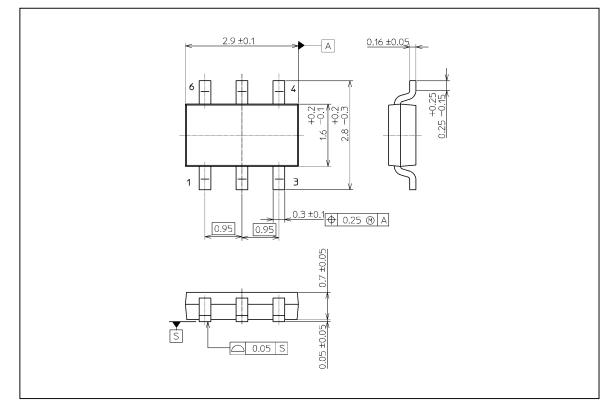


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### TPC6130

#### **Package Dimensions**

Unit: mm



#### Weight: 0.011 g (typ.)

|                 | Package Name(s) |
|-----------------|-----------------|
| TOSHIBA: 2-3T1S |                 |
| Nickname: VS-6  |                 |

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